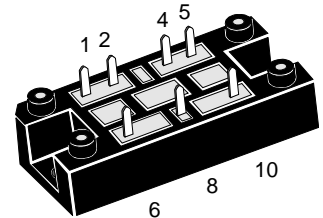
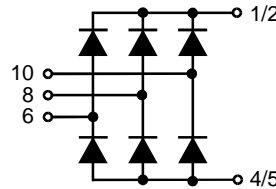


Three Phase Rectifier Bridge

$I_{dAVM} = 55 \text{ A}$
 $V_{RRM} = 800-1800 \text{ V}$

V_{RSM} V	V_{RRM} V	Type
900	800	VUO 52-08NO1
1300	1200	VUO 52-12NO1
1500	1400	VUO 52-14NO1
1700	1600	VUO 52-16NO1
1900	1800	VUO 52-18NO1



Symbol	Test Conditions	Maximum Ratings	
I_{dAV}	$T_K = 90^\circ\text{C}$, module	54	A
I_{dAV}	$T_A = 45^\circ\text{C}$ ($R_{thKA} = 0.5 \text{ K/W}$), module	43	A
I_{dAVM}	module	55	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	350 A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	375 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	305 A
		$t = 8.3 \text{ ms}$ (60 Hz), sine	325 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	615 A ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	590 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms}$ (50 Hz), sine	465 A ² s
		$t = 8.3 \text{ ms}$ (60 Hz), sine	445 A ² s
T_{VJ}		-40...+130	°C
T_{VJM}		130	°C
T_{stg}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$	3000 V~
		$t = 1 \text{ s}$	3600 V~
M_d	Mounting torque (M5) (10-32UNF)	2 - 2.5	Nm
		18-22	lb.in.
Weight	typ.	35	g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered E72873

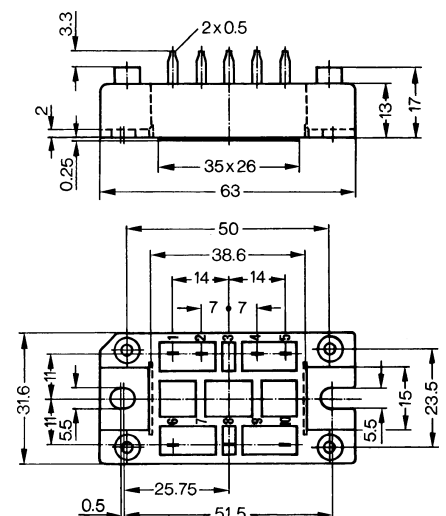
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Data according to IEC 60747 and refer to a single diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions.

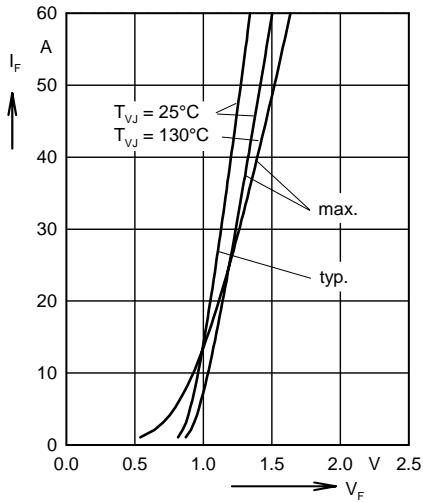


Fig. 1 Forward current versus voltage drop per diode

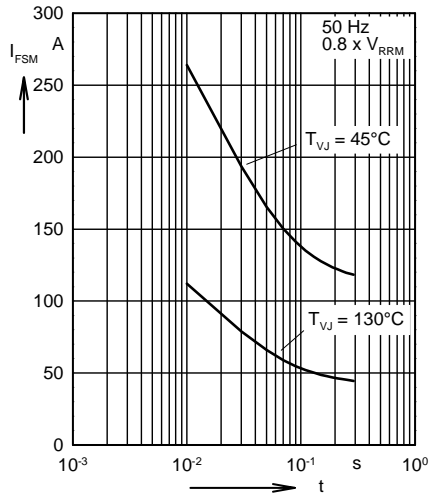


Fig. 2 Surge overload current per diode
I_{FSM}: Crest value. t: duration

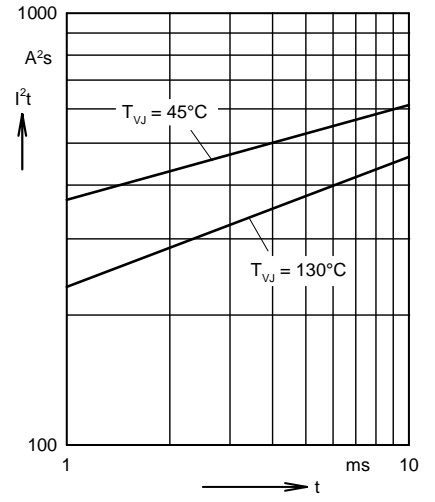


Fig. 3 I²t versus time (1-10 ms) per diode

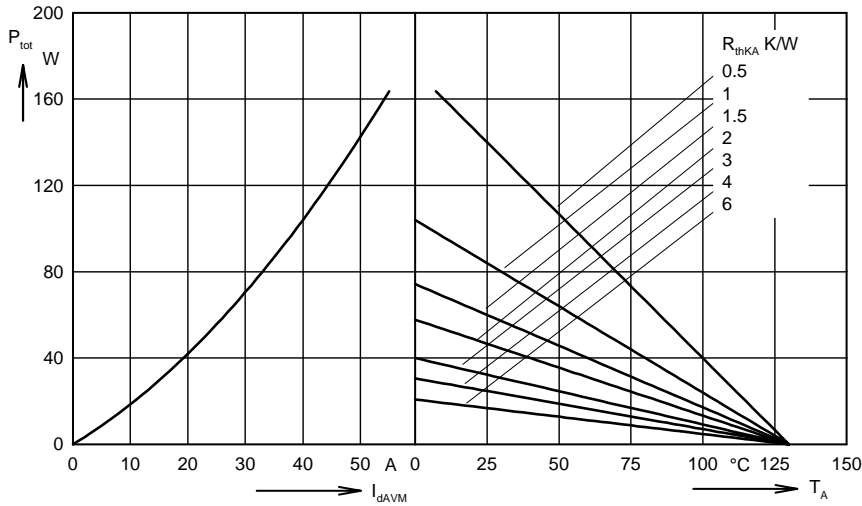


Fig. 4 Power dissipation versus direct output current and ambient temperature

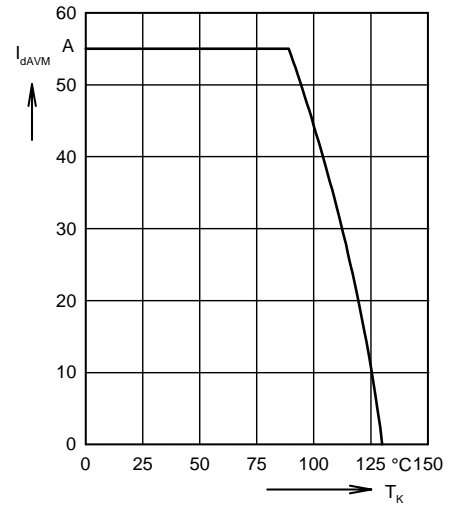


Fig. 5 Maximum forward current at heatsink temperature T_K

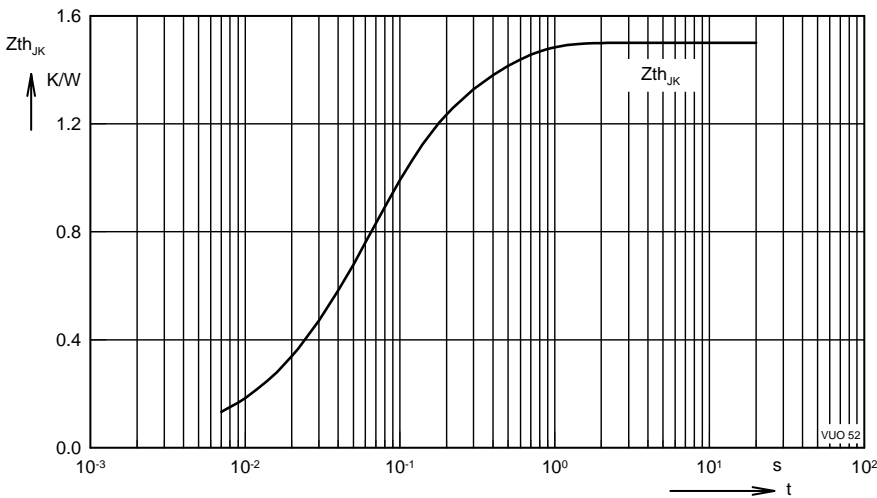


Fig. 6 Transient thermal impedance junction to heatsink per diode

Constants for Z_{thJK} calculation:

i	R _{th} (K/W)	t _i (s)
1	0.005	0.008
2	0.2	0.05
3	0.845	0.06
4	0.45	0.3